

Index-Guided High Power AlGaAs Laser Diode

Description

The SLD233VL is a high power index-guided AlGaAs laser diode.

Features

- Low noise
- Low power consumption

Applications

Pickups for MiniDisc recording/playback

Structure

- AlGaAs quantum well-structure laser diode
- PIN photodiode for optical power output monitor

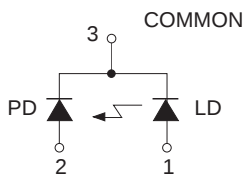
Recommended Operating Optical Power Output

30mW

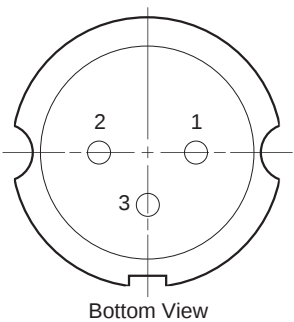
Absolute Maximum Ratings (Tc = 25°C)

- | | | | |
|-------------------------|------------------|------------|----|
| • Optical power output | P _o | 35 | mW |
| • Reverse voltage | V _R | LD 2 | V |
| | | PD 15 | V |
| • Operating temperature | T _{opr} | −10 to +60 | °C |
| • Storage temperature | T _{stg} | −40 to +85 | °C |

Connection Diagram



Pin Configuration



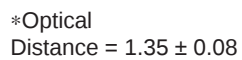
- 1. LD ANODE
- 2. PD ANODE
- 3. COMMON

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Optical and Electrical Characteristics (T_c = 25°C)T_c: Case temperature

Item		Symbol	Conditions	Min.	Typ.	Max.	Unit
Threshold current		I _{th}			30	40	mA
Operating current		I _{op}	P _O = 35mW		70	85	mA
Operating voltage		V _{op}	P _O = 35mW		2.0	2.5	V
Oscillation wavelength		λ	P _O = 35mW	780	790	800	nm
Radiation angle	Perpendicular	θ⊥	P _O = 35mW	26	28.5	32	degree
	Parallel	θ//		7.4	8.5	10.0	degree
Positional accuracy	Position	ΔX, ΔY, ΔZ	P _O = 35mW			±80	μm
	Angle	Δφ⊥				±3	degree
		Δφ//				±2	degree
Differential efficiency		ηD	P _O = 30mW	0.55	0.9	1.2	mW/mA
Astigmatism		As			−16		μm
Coherence		γ	P _O = 4mW		0.7	0.9	

Unit: mm



PACKAGE WEIGHT	0.3g
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